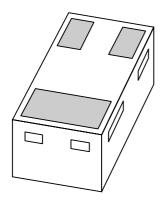
DISCRETE SEMICONDUCTORS

DATA SHEET



BAT54CMSchottky barrier double diode

Product data sheet 2003 Nov 11



Schottky barrier double diode

BAT54CM

FEATURES

- Low forward voltage
- Leadless ultra small plastic package $(1.0 \times 0.6 \times 0.5 \text{ mm})$
- Boardspace 1.17 mm² (approx. 10% of SOT23)
- Power dissipation comparable to SOT23.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- Mobile communications, digital (still) cameras, PDAs and PCMCIA cards.

DESCRIPTION

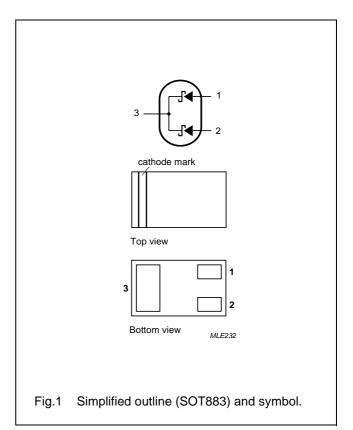
Planar Schottky barrier double diode encapsulated in a SOT883 leadless ultra small plastic package.

MARKING

TYPE NUMBER	MARKING CODE
BAT54CM	S 3

PINNING

PIN	DESCRIPTION	
1	anode (a ₁)	
2	anode (a ₂)	
3	common cathode	



ORDERING INFORMATION

TYPE NUMBER	PACKAGE			
TIFE NOWIBER	NAME	DESCRIPTION	VERSION	
BAT54CM	_	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5$ mm	SOT883	

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Schottky barrier double diode

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		_	30	V
I _F	continuous forward current		-	200	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	_	300	mA
I _{FSM}	non-repetitive peak forward current	t _p < 10 ms	_	600	mA
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
P _{tot}	total power dissipation (per package)	T _{amb} ≤ 25 °C; note 1	_	250	mW

Note

1. Refer to SOT883 standard mounting conditions (footprint); FR4 with 60 μm copper strip line.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60 μm copper strip line.

Soldering

Reflow soldering is the only recommended soldering method.

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V _F	forward voltage	see Fig.2;		
		$I_{F} = 0.1 \text{ mA}$	240	mV
		I _F = 1 mA	320	mV
		I _F = 10 mA	400	mV
		$I_F = 30 \text{ mA}$	500	mV
		I _F = 100 mA	800	mV
I _R	continuous reverse current	V _R = 25 V; note 1; see Fig.3	2	μΑ
C _d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 1 \text{ V}$; see Fig.4	10	pF

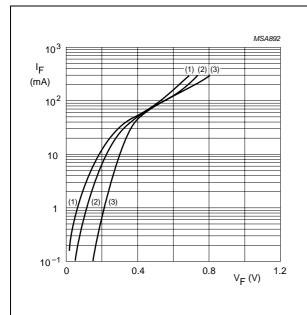
Note

1. Pulsed test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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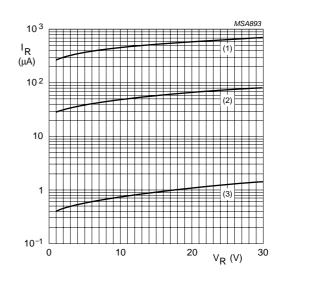
Schottky barrier double diode

BAT54CM



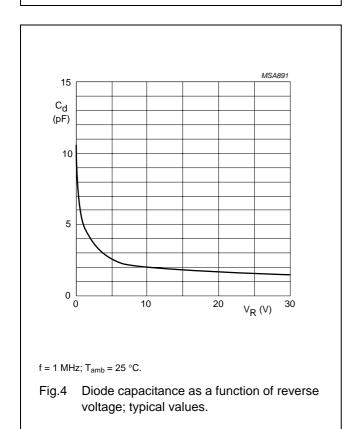
- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



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Schottky barrier double diode

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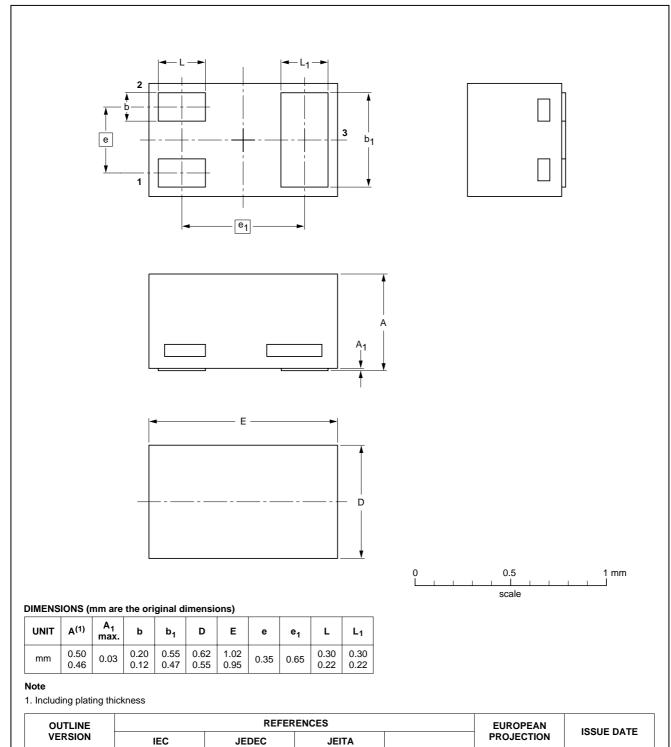
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03-04-03

PACKAGE OUTLINE

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



SC-101

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SOT883

Schottky barrier double diode

BAT54CM

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

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